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Japanese Patent Laid-Open Publication No. Heisei 9-8205

[TITLE OF THE INVENTION]

RESIN-ENCAPSULATED SEMICONDUCTOR DEVICE

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[CLAIMS]

1. A resin-encapsulated semiconductor device using
a lead frame which is shaped in accordance with a two-step
etching process to a body wherein a thickness of inner
10 leads is less than that of the lead frame blank,
comprising:

inner leads having the thickness less than that of the
lead frame blank; and

terminal columns integrally connected to the inner
15 leads and having the same thickness with the lead frame
blank, the terminal columns possessing a column-shaped
configuration which is adapted to be electrically connected
to an external circuit, the terminal columns being disposed
outside of the inner leads in a manner such that they are
20 coupled to the inner leads in a direction orthogonal to the
thickness-wise direction thereof, the terminal columns
having terminal portions arranged on top ends thereof, the
terminal portions being made of solders, etc. and exposed
to the outside beyond a resin encapsulate, each inner lead
25 possessing a rectangular cross-section and having four

surfaces including a first surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

2. A resin-encapsulated semiconductor device using a lead frame which is shaped in accordance with a two-step etching process to a body wherein a thickness of inner leads is less than that of the lead frame blank, comprising:

inner leads having the thickness less than that of the lead frame blank; and

terminal columns integrally connected to the inner leads and having the same thickness with the lead frame blank, the terminal columns possessing a column-shaped configuration which is adapted to be electrically connected to an external circuit, the terminal columns being disposed outside of the inner leads in a manner such that they are coupled to the inner leads in a direction orthogonal to the thickness-wise direction thereof, portions of top ends of the terminal columns being exposed to the outside beyond a resin encapsulate, each inner lead possessing a rectangular

cross-section and having four surfaces including a first surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank, while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

10 3. The resin-encapsulated semiconductor device as claimed in claims 1 or 2, wherein a semiconductor chip is received inward of the inner leads, and electrodes of the semiconductor chip are electrically connected to the inner leads through wires, respectively.

15 4. The resin-encapsulated semiconductor device as claimed in claim 3, wherein the lead frame has a die pad, and the semiconductor chip is mounted onto the die pad.

20 5. The resin-encapsulated semiconductor device as claimed in claim 3, wherein the lead frame does not have a die pad, and the semiconductor chip is fastened to the inner leads using a reinforcing fastener tape.

25 6. The resin-encapsulated semiconductor device as

claimed in claims 1 or 2, wherein the semiconductor chip is fastened by means of insulating adhesive to the second surfaces of the inner leads on one surface thereof on which the electrodes are located, and the electrodes of the semiconductor chip are electrically connected to the first surfaces of the inner leads through wires, respectively.

7. The resin-encapsulated semiconductor device as claimed in claims 1 or 2, wherein the semiconductor chip is fastened to the second surfaces of the inner leads by bumps thereby to be electrically connected to the inner leads.

[DETAILED DESCRIPTION OF THE INVENTION]

[FIELD OF THE INVENTION]

The present invention relates to a resin-encapsulated semiconductor device capable of meeting the requirement for an increase in the number of terminals and resolving problems which are caused in association with position shift and coplanarity of an outer lead.

[DESCRIPTION OF THE PRIOR ART]

FIG. 15(a) shows the configuration of a generally known resin-encapsulated semiconductor device (a plastic lead frame package). The shown resin-encapsulated semiconductor device includes a die pad 1511 having a

semiconductor chip 1520 mounted thereon, outer leads 1513
to be electrically connected to the associated circuits,
inner leads 1512 formed integrally with the outer leads
1513, bonding wires 1530 for electrically connecting the
5 tips of the inner leads 1512 to the bonding pad 1521 of the
semiconductor chip 1520, and a resin 1540 encapsulating the
semiconductor chip 1520 to protect the semiconductor chip
1520 from external stresses and contaminants. This resin-
encapsulated semiconductor device, after mounting the
10 semiconductor chip 1520 on the bonding pad 1521, is
manufactured by encapsulating the semiconductor chip 1520
with the resin. In this resin-encapsulated semiconductor
device, the number of the inner leads 1512 is equal to that
of the bonding pads 1521 of the semiconductor chip 1520.
15 And, FIG. 15(b) shows the configuration of a monolayer lead
frame used as an assembly member of the resin-encapsulated
semiconductor device shown in FIG. 15a. Such a lead frame
includes the bonding pad 1511 for mounting the
semiconductor chip, the inner leads 1512 to be electrically
20 connected to the semiconductor chip, the outer lead 1513
which is integral with the inner leads 1512 and is to be
electrically connected to the associated circuits. This
also includes dam bars 1514 serving as a dam when
encapsulating the semiconductor chip with the resin, and a
25 frame 1515 serving to support the entire lead frame 1510.

Such a lead frame is formed from a highly conductive metal
such as a cobalt, 42 alloy (a 42% Ni-Fe alloy), copper-based
alloy by a pressing working process or an etching process.
FIG. 15(b)(D) is a cross-sectional view taken along the
5 line F1-F2 of FIG. 15(b)(1).

Recently, there has been growing demand for the
miniaturization and reduction in thickness of resin-
encapsulated semiconductor device employing lead frames
like the lead frame (plastic lead frame package) and the
10 increase of the number of terminals of resin-encapsulated
semiconductor package as electronic apparatuses are
miniaturized progressively and the degree of the
integration of semiconductor device increase progressively.
Thus, recent resin-encapsulated semiconductor package,
15 particularly quad plate package (QFPs) and thin quad flat
packages (TQFPs) have each a greatly increased number of
pins.

Lead frames having inner leads arranged at small
20 pitches among lead frames for semiconductor packages are
fabricated by a photolithographic etching process, while
lead frames having inner leads arranged at comparatively
large pitches among lead frames for semiconductor packages
are fabricated by press working. However, lead frames
having a large number of fine inner leads to be used for
25 forming semiconductor packages having a large number of

pins are fabricated by subjecting a blank of a thickness on the order of 0.25 mm to an etching process, not a press working.

5 The etching process for forming a lead frame having fine inner leads will be described hereinafter with reference to FIG. 14. First, a copper alloy or 42 alloy thin sheet of a thickness on the order of 0.25 mm (a lead frame blank 1410) is cleaned perfectly (FIG. 14(a)). Then, a photoresist, such as a water-soluble casein photoresist containing potassium dichromate as a sensitive agent, is spread in photoresist films 1420 over the major surfaces of the thin film as shown in FIG. 14(b).

10 Then, the photoresist films are exposed, through a mask of a predetermined pattern, to light emitted by a high-pressure mercury lamp, and the thin sheet is immersed in a developer for development to form a patterned photoresist film 1430 as shown in FIG. 14(c). Then, the thin sheet is subjected, when need be, to a hardening process, a washing process and such, and then an etchant containing ferric chloride as a principal component is sprayed against the thin sheet 1410 to etch through portions of the thin sheet 1410 not coated with the patterned photoresist films 1420 so that inner leads of predetermined sizes and shapes are formed as shown in FIG. 14(d).

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Then, the patterned resist films are removed, the patterned thin sheet 1410 is washed to complete a lead frame having the inner leads of desired shapes as shown in FIG. 14(e). Predetermined areas of the lead frame thus
5 formed by the etching process are silver-plated. After being washed and dried, an adhesive polyimide tape is stuck to the inner leads for fixation, predetermined tab bars are bent, when need be, and the die pad depressed. In the etching process, the etchant etches the thin sheet in both
10 the direction of the thickness and directions perpendicular to the thickness, which limits the miniaturization of inner lead pitches of lead frames. Since the thin sheet is etched from both the major surfaces as shown in FIG. 14 during the etching process, it is said, when the lead frame
15 has a line-and-space shape, that the smallest possible intervals between the lines are in the range of 50 to 100% of the thickness of the thin sheet. From the viewpoint of forming the outer lead having a sufficient strength, generally, the thickness of the thin sheet must be about
20 0.125 mm or above. Furthermore, the width of the inner leads must be in the range of 70 to 80 μ m for successful wire bonding. When the etching process as illustrated in FIG. 14 is employed in fabricating a lead frame, a thin sheet of a small thickness in the range of 0.125 to 0.15 mm
25 is used and inner leads are formed by etching so that the

fine tips thereof are arranged at a pitch of about 0.1 mm.

However, recent miniature resin-encapsulated semiconductor package requires inner leads arranged
5 pitches in the range of 0.13 to 0.15 mm, far smaller than 0.165 mm. When a lead frame is fabricated by processing thin sheet of a reduced thickness, the strength of the outer leads of such a lead frame is not large enough
10 to withstand external forces that may be applied thereto in the subsequent processes including an assembling process and a chip mounting process. Accordingly, there is a limit to the reduction of the thickness of the thin sheet to enable the fabrication of a minute lead frame having fine leads arranged at very small pitches by etching.

15 An etching method previously proposed to overcome such difficulties subjects a thin sheet to an etching process to form a lead frame after reducing the thickness of portions of the thin sheet corresponding to the inner leads of the lead frame by half etching or pressing to form
20 the fine inner leads by etching without reducing the strength of the outer leads. However, problems arise in accuracy in the subsequent processes when the lead frame is formed by etching after reducing the thickness of the portions corresponding to the inner leads by pressing; for
25 example, the smoothness of the surface of the plated areas

is unsatisfactory, the inner leads cannot be formed in a flatness and a dimensional accuracy required to clamp the lead frame accurately for bonding and molding, and a platemaking process must be repeated twice making the lead fabricating process intricate. It is also necessary to repeat a platemaking process twice when the thickness of the portions of the thin sheet corresponding to the inner leads is reduced by half etching before subjecting the thin sheet to an etching process for forming the lead frame, which also makes the lead frame fabricating process intricate. Thus, this previously proposed etching method has not yet been applied to practical lead frame fabricating processes.

(SUBJECT MATTERS TO BE SOLVED BY THE INVENTION)

On the other hand, because a pitch among inner leads is made narrow as the number of terminals is increased, it is considered important to know whether a problem is caused or not in association with position shift or coplanarity of an outer lead when implementing a chip mounting process. Accordingly, the present invention has been made in an effort to solve the problems occurring in the related art, and an object of the present invention is to provide a resin-encapsulated semiconductor device capable of meeting the requirement for an increase in the number of terminals

and resolving problems which are caused in association with position shift and coplanarity of an outer lead.

(MEANS FOR SOLVING THE SUBJECT MATTERS)

5 According to one aspect of the present invention, there is provided a resin-encapsulated semiconductor device using a lead frame which is shaped in accordance with a two-step etching process to a body wherein a thickness of inner leads is less than that of the lead frame blank, comprising: inner leads having the thickness less than
10 of the lead frame blank; and terminal columns electrically connected to the inner leads and having the same thickness as with the lead frame blank, the terminal columns being disposed in a column-shaped configuration which is adapted to be
15 electrically connected to an external circuit, the terminal columns being disposed outside of the inner leads in a manner such that they are coupled to the inner leads in a direction orthogonal to the thickness-wise direction thereof, the terminal columns having terminal portions
20 arranged on top ends thereof, the terminal portions being made of solders, etc. and exposed to the outside beyond the resin encapsulate, outer surfaces of the terminal columns also being exposed to the outside beyond the resin encapsulate, each inner lead possessing a rectangular
25 cross-section and having four surfaces including a

surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

According to another aspect of the present invention there is provided a resin-encapsulated semiconductor device using a lead frame which is shaped in accordance with a two-step etching process to a body wherein a thickness of inner leads is less than that of the lead frame blank comprising: inner leads having the thickness less than that of the lead frame blank; and terminal columns integrally connected to the inner leads and having the same thickness with the lead frame blank, the terminal columns possessing a column-shaped configuration which is adapted to be electrically connected to an external circuit, the terminal columns being disposed outside of the inner leads in a manner such that they are coupled to the inner leads in a direction orthogonal to the thickness-wise direction thereof, portions of top ends of the terminal columns being exposed to the outside beyond a resin encapsulate, outer surfaces of the terminal columns also being exposed to the outside beyond the resin encapsulate, each inner lead

possessing a rectangular cross-section and having four surfaces including a first surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

According to another aspect of the present invention, a semiconductor chip is received inward of the inner leads, and electrodes (pads) of the semiconductor chip are electrically connected to the inner leads through wires, respectively. According to another aspect of the present invention, the lead frame has a die pad, and the semiconductor chip is mounted onto the die pad. According to another aspect of the present invention, the lead frame does not have a die pad, and the semiconductor chip is fastened to the inner leads using a reinforcing fastener tape. According to still another aspect of the present invention, the semiconductor chip is fastened by means of insulating adhesive to the second surfaces of the inner leads on one surface thereof on which the electrodes are located, and the electrodes of the semiconductor chip are electrically connected to the first surfaces of the inner leads through wires, respectively. According to yet still

another aspect of the present invention, the semiconductor chip is fastened to the second surfaces of the inner leads by bumps thereby to be electrically connected to the inner leads. In the above descriptions, in the case that the terminal columns have terminal portions which are arranged on top ends of the terminal columns, with the terminal portions made of solders, etc. and exposed to the outside beyond the resin encapsulate, while it is the norm that the terminal portions comprising the solders, etc. are exposed to the outside beyond the resin encapsulate, it is not necessarily required for the terminal portions to be projected beyond the resin encapsulate. Moreover, while it is possible to use the outside surfaces of the terminal columns while they are not encapsulated by the resin encapsulate and they are exposed to the outside, the outside surfaces of the terminal columns which are not encapsulated by the resin encapsulate, can be covered by a protective frame using adhesive, etc.

20 [WORKING FUNCTIONS]

The resin-encapsulated semiconductor device in accordance with the present invention can meet a demand for an increase in the number of terminals. At the same time, in the resin-encapsulated semiconductor device, because the forming process of the outer leads as in the case of using

a mono-layered lead frame shown in FIG. 13(b) is not required, it is possible to provide a semiconductor device in which no problems are caused in association with position shift and coplanarity of the outer leads. More particularly, the use of a multi-pinned lead frame shaped in a manner that inner leads have a thickness less than that of the lead frame blank by a two-step etching process, that is, the inner leads are arranged at a fine pitch, can meet a demand for an increase in the pin number of the semiconductor device. Furthermore, by using the lead frame which is fabricated by a two-step etching process as will be described later with reference to FIG. 1, the second surface of each inner lead has coplanarity, and is excellent in wire-bonding property. In addition, since the first surface of the inner lead is also a flat surface and the third and fourth surfaces are depressed toward the inside of the inner lead, the inner leads are stable and coplanarity width upon wire bonding process can be enlarged.

[EMBODIMENTS]

Embodiments of the resin-encapsulated semiconductor device in accordance with the present invention will now be described with reference to the attached drawings. First, a resin-encapsulated semiconductor device in accordance

With a first embodiment of the present invention described hereinafter with reference to FIGS. 1, FIG. 1(a) is a cross-sectional view of the encapsulated semiconductor device according to the embodiment of the present invention. FIG. 1(b) is a sectional view of an inner lead taken along the line of FIG. 1(a), and FIG. 1(c) is a cross-sectional view of a terminal column taken along the line B1-B2 of FIG. 1. Moreover, FIG. 2(a) is a perspective view of the encapsulated semiconductor device according to the embodiment of the present invention, FIG. 2(b) is a view of the resin-encapsulated semiconductor device of FIG. 2(a), and FIG. 2(c) is a bottom view of the encapsulated semiconductor device of FIG. 2(a). In FIGS. 1 and 2, a drawing reference numeral 100 represents a resin-encapsulated semiconductor device, 110 a semiconductor chip, 111 electrodes (pads), 120 wires, 130 a lead frame, 131 inner leads, 131Aa a first surface, 131Ab a second surface, 131Ac a third surface, 131Ad a fourth surface, 133A terminal columns, 133B terminal portions, 133C side surfaces, 133D a bottom surface, 135 a die pad, and 140 resin encapsulate.

In the resin-encapsulated semiconductor device according to the first embodiment, as shown in FIG. 1, the semiconductor chip 110 is placed inward of the

leads 131. As can be readily seen from FIG. 1(a), the semiconductor chip 110 is mounted on the die pad 135 at one surface thereof which is opposed to the other surface thereof where the electrodes pads 111 of the semiconductor chip 110 are arranged. Each electrode pad 111 is electrically connected to the second surface 131a of the inner lead 131 through the wire 120. The electrical connection between the resin-encapsulated semiconductor device 100 of this embodiment and an external circuit is achieved by mounting the resin-encapsulated semiconductor device 100 via the terminal portions 133a each being made of a semi-spherical solder, on a printed circuit substrate, with the terminal portions 133a located on the top surfaces 133b of the terminal columns 133, respectively. In the resin-encapsulated semiconductor device of the first embodiment of the present invention, it is not necessarily required to provide a protective frame 190, and instead, a structure, as shown in FIG. 1(d), in which no protective frame is used can be adopted.

The lead frame 130 used in the semiconductor device 100 according to the first embodiment is made of a 42% nickel-iron alloy. Therefore, the lead frame 130A which has a contour as shown in FIG. 9(a) and is shaped by an etching process, is used as the lead frame 130. The lead frame 130 has inner leads 131 which are shaped to have a

thickness less than that of the terminal columns 133 or other portions. Dam bars 136 serve as a dam when encapsulating the semiconductor chip 110 with a resin. Moreover, although the lead frame 130A which is processed by etching to have the contour as shown in FIG. 2A is used in this embodiment, the lead frame is not limited to such a contour because portions except the inner leads 131 and the terminal columns 133 are not necessary. The inner leads 131 have a thickness of 40 μ m whereas the portions of the lead frame 130 other than the inner leads 131 have a thickness of 0.15 mm which corresponds to the thickness of the lead frame blank. The other portions of the lead frame 130 except the inner leads 131 may not have the thickness of 0.15 mm, but have a thickness of 0.125 mm-0.50 mm which is thinner. The tips of the inner leads 131 have a small pitch of 0.12 mm so as to achieve an increase in the number of terminals for semiconductor devices. The second face 131Ab of the inner lead 131 has a substantially flat profile so as to allow an easy wire bonding thereon. Also, as shown in FIG. 1(b), because the third and fourth faces 131Ac and 131Ad have a concave shape which is depressed toward the inside of the associated inner lead, a high strength can be obtained even though the second face (wire bonding surface) 131Ab is narrowed.

In the present embodiment, since twisting does not

occur in the inner leads 131 irrespective of whether the
inner leads 131 is long or not. The inner leads having the
contour, as shown in FIG. 9(a), in which the tips of the
inner leads 131 are separated one from another, are
5 prepared by the etching process, and the inner leads are
resin-encapsulated after mounting the semiconductor chip
thereon as will be described later. However, where the
inner leads 131 are long in their length and have a
tendency for the generation of twisting therein, it is
10 impossible to fabricate the lead frame by etching to have
the contour as shown in FIG. 9(a). Therefore, after
etching the lead frame in a state where the tips of the
inner leads are fixed to the connecting portion 131B as
shown in FIG. 9(c)(1), the inner leads 131 are fixed with
15 the reinforcing tape 160 as shown in FIG. 9(c)(2). Then,
the connecting portions 131B which are not necessary in the
fabrication of the resin-encapsulated semiconductor device
are removed by a press as shown in FIG. 9(c)(3), and a
semiconductor device is then mounted on the lead frame.

20 Hereinafter, a method for the fabrication of the
resin-encapsulated semiconductor device will now be
described with reference to FIG. 8. First, the lead frame
130A, as shown in FIG. 9(a), which is shaped by the etching
process as will be described later, is prepared such that
25 the second surfaces 131Ab of the inner leads 131 are

directed upward (FIG. 8(a)).

Then, the semiconductor chip 110 is mounted onto the die pad 135 such that the surfaces of the semiconductor chip 110 on which the electrodes 111 are arranged, are directed upward (FIG. 8(b)).

Next, after the semiconductor chip 110 is fastened onto the die pad 135, the electrodes 111 of the semiconductor chip 110 and the second surfaces 131Ab of the inner leads 131 are bonded with each other using wires 112 (FIG. 8(c)).

Subsequently, encapsulation is carried out with the conventional resin encapsulate 140. Thereafter, unnecessary portions of the lead frame 130 which are protruded from the resin encapsulate 140 are cut by a press to form terminal columns 133 and also the side surfaces 133B of the terminal columns 133 (FIG. 8(d)).

Then, the dam bars 126, the frame portions 137, etc. of the lead frame 130A as shown in FIG. 9 are removed. Next, the terminal portions 133A each made of the semi-spherical solder are arranged on the outer surface of each terminal column 133 to fabricate a resin-encapsulated semiconductor device (FIG. 8(e)).

Thereafter, the protective frame 180 is arranged by means of adhesive around an entire outer surface of the resultant structure in such a manner that the side surfaces

of the terminal columns 133 are covered thereby FIG. 6(f)). At this time, the protective frame 180 functions to reinforce the semiconductor device. In other words, the protective frame 180 serves to prevent moisture from
5 leaking into a gap between the resin encapsulate and the terminal columns due to the fact that the side surfaces of the terminal columns are exposed to the outside, whereby a crack is not formed in the semiconductor device and the breakage of the semiconductor device is avoided. However,
10 persons skilled in the art will readily appreciate that it is not necessarily required to provide the protective frame 180. Also, when such an encapsulating process by the resin is carried out using a desired mold, the encapsulating process is implemented in a state wherein the outer side
15 surfaces of the terminal columns of the lead frame are somewhat protruded out of the resin encapsulate.

A method for etching the lead frame of the first embodiment will now be described in conjunction with the attached drawings. FIG. 11 is of cross-sectional views
20 respectively illustrating sequential steps of the etching process for the lead frame of the first embodiment. In particular, the cross-sectional views of FIG. 1 correspond to a cross section taken along the line D1-D2 of FIG. 9(a). In FIG. 11, the reference numeral 1110 denotes a lead frame
25 blank, 1120A and 1120B resist patterns, 1130 first opening,

1140 second openings, 1150 first concave portions, 1160 second concave portions, 1170 flat surfaces, and 1180 an etch-resistant layer. First, a water-soluble casein resist using potassium dichromate as a sensitive agent is coated
5 over both surfaces of the lead frame blank 1110 made of a 42% nickel-iron alloy and having a thickness of about 0.15 mm. Using desired pattern plates, the resist films are patterned to form resist patterns 1120A and 1120B having first opening 1130 and second openings 1140, respectively
10 (FIG. 11(a)).

The first opening 1130 is adapted to etch the lead frame blank 1110 to have a flat etched bottom surface to a thickness smaller than that of the lead frame blank 1110 in a subsequent process. The second openings 1140 are adapted
15 to form desired shapes of tips of inner leads. Although the first opening 1130 includes at least an area forming the tips of the inner leads 1110, a topology generated by partially thinned portion by etching in a subsequent process can cause hindrance in a taping process or a
20 clamping process for fixing the lead frame. Thus, an area to be etched needs to be large without being limited to fine portions of the tips of the inner leads. Thereafter, both surfaces of the lead frame blank 1110 formed with the resist patterns are etched using a 48 Be' ferric chloride
25 solution of a temperature of 57°C at a spray pressure of

2.5 kg/cm². The etching process is terminated at the point of time when first recesses 1150 etched to have a flat etched bottom surface have a depth h corresponding to $1/3$ of the thickness of the lead frame blank (FIG. 11 b).

5 Although both surfaces of the lead frame blank 1110 are simultaneously etched in the primary etching process, it is not necessary to simultaneously etch both surfaces of the lead frame blank 1110. The reason why both surfaces of the lead frame blank 1110 are simultaneously etched, as in
10 this embodiment, is to reduce the etching time taken in a secondary etching process as will be described later. The total time taken for the primary and secondary etching processes is less than that taken in the case of etching of only one surface of the lead frame blank on which the resist pattern 1120B is formed. Subsequently, the surface
15 provided with the first recesses 1150 respectively etched at the first opening 1130 is entirely coated with an etch-resistant hot-melt wax (acidic wax type MR-WB6, The Inctec Inc.) by a die coater to form an etch-resistant layer 1180 so as to fill up the first recesses 1150 and to
20 cover the resist pattern 1120A (FIG. 11(c)).

It is not necessary to coat the etch-resistant layer 1180 over the entire portion of the surface provided with the resist pattern 1120A. However, it is preferred that
25 the etch-resistant layer 1180 be coated over the entire

portion of the surface formed with the first recess
and first opening 1130, as shown in FIG. 11(c), because
it is difficult to coat the etch-resistant layer 1180 on
the surface portion including the first recesses.
5 Although the etch-resistant layer 1180 wax employed in
this embodiment is an alkali-soluble wax, any material
resistant to the etching action of the etchant solution
remaining somewhat soft during etching may be used.
for forming the etch-resistant layer 1180 is not limited
10 to the above-mentioned wax, but may be a wax of a UV-se
type. Since each first recess 1130 etched by the pre-
etching process at the surface formed with the paste
adapted to form a desired shape of the inner lead is
filled up with the etch-resistant layer 1180, it is
15 further etched in the following secondary etching process.
The etch-resistant layer 1180 also enhances the mechanical
strength of the lead frame blank for the second etching
process, thereby enabling the second etching process to
be conducted while keeping a high accuracy. It is
20 possible to enable a second etchant solution to be sprayed
at an increased spraying pressure, for example, 2.5 kg
or above, in the secondary etching process. The increased
spraying pressure promotes the progress of etching in the
direction of the thickness of the lead frame blank in
25 the secondary etching process. Then, the lead frame blank

subjected to a secondary etching process. In this secondary etching process, the lead frame blank 1110 is etched at its surface formed with first recesses 1130 having a flat etched bottom surface, to completely perforate the second recesses 1160, thereby forming the tips of inner leads 131A (FIG. 11.5)).

The bottom surface 1170 of each recess formed by the primary etching process is flat. However, both side surfaces of each recess positioned at opposite sides of the bottom surface 1170 have a concave shape depressed toward the inside of the inner lead. Then, the lead frame blank is cleaned. After completion of the cleaning process, the etch-resistant layer 1180, and resist films (resist patterns 1120A and 1120B) are sequentially removed. Thus, a lead frame 130A having a structure of FIG. 9(a) is obtained in which tips of the inner leads 131A are arranged at a fine pitch. The removal of the etch-resistant layer 1180 and resist films (resist patterns 1120A and 1120B) is achieved using a sodium hydroxide solution serving to dissolve them.

The processes for manufacturing the lead frame as shown in FIG. 11, is to form by means of etching the lead frame having the tips of the inner leads used in this embodiment of the present invention, which have a thickness less than that of the lead frame. Especially, the first

surfaces 131Aa of the tips of the inner leads as shown in
FIG. 1, are flushed with one surfaces of remaining portions
of the inner leads having the same thickness with the lead
frame while being opposed to the second surfaces 131Ab, and
the third and fourth surfaces are formed to have a concave
shape which is depressed toward the inside of the inner
leads. Where a semiconductor chip is mounted on the second
surfaces 131Ab of the inner leads by means of bumps for an
electrical connection therebetween, as in a semiconductor
device according to a third embodiment as will be described
hereinafter, an increased tolerance for the connection by
bumps is obtained when the second surface 131Ab has a
concave shape depressed toward the inside of the inner
lead. To this end, an etching method shown in FIG. 12 is
adopted in this case. The etching method shown in FIG. 12
is the same as that of FIG. 11 in association with its
primary etching process. After completion of the primary
etching process, the etching method is conducted in a
manner different from that of the etching method of FIG. 11
in that the second etching process is conducted at the side
of the first recesses 1150 after filling up the second
recesses 1160 by the etch-resist layer 1180, thereby
completely perforating the second recesses 1160. At this
time, by implementing the primary etching process, etching
at the side of the second openings 1140 is performed in a

sufficient manner. The cross section of each inner lead, including its tip, formed in accordance with the etching method of FIG. 12, has a concave shape depressed toward the inside of the inner lead at the second surface 131Ab, as shown in FIG. 6(b).

The etching method in which the etching process is conducted at two separate steps, respectively, as in that of FIGs. 11 and 12, is generally called a "two-step etching method". This etching method is advantageous in that a desired fineness can be obtained. The etching method used to fabricate the lead frame 130A of the first embodiment shown in FIG. 9 involves the two-step etching method and the method for forming a desired shape of each lead frame portion while reducing the thickness of each pattern formed. In particular, the etching method makes it possible to achieve a desired fineness. In accordance with the method illustrated in FIGs. 11 and 12, the fineness of the tip of each inner lead 131A formed by this method is dependent on the shape of the second recesses 1160 and the thickness t of the inner lead tip which is finally obtained. For example, where the blank has a thickness t reduced to 50 μm , the inner leads can have a fineness corresponding to a lead width W_1 of 100 μm and a tip pitch p of 0.15 mm, as shown in FIG. 11(e). In the case of using a small blank thickness t of about 30 μm and a lead

width W_1 of 70 μm , it is possible to form inner leads having a fineness corresponding to an inner lead pitch p of 0.12 mm. Of course, it may be possible to form inner leads having a further reduced tip pitch by adjusting the blank thickness t and the lead width W_1 . That is to say, an inner lead tip pitch p up to 0.08 mm, a blank thickness up to 25 μm , and a lead width W_1 up to 40 μm can be obtained.

In the case where twisting of the inner leads does not occur in the fabricating process, as in the case where the inner leads are short in their length, a lead frame illustrated in FIG. 9(a) can be directly obtained. However, where the inner leads are long in length as compared to those of the first embodiment, the inner leads have tendency for the generation of twisting. Thus, in this case, the lead frame is obtained by etching in a state where the tips of the inner leads are bound to each other by a connecting member 131B as shown in FIG. 9(c)(1). Then, the connecting member 131B which is not necessary for the fabrication of a semiconductor package is cut off by means of a press to obtain a lead frame shaped as shown in FIG. 9(a).

Moreover, as described above, where unnecessary portions in a structure shown in FIG. 9(c)(1) are cut to obtain the lead frame having the contour shown in FIG.

9(a), a reinforcing tape 160 (a polyimide tape is generally used, as shown in FIG. 9(b)(A)). While the connecting member 131B is cut off by means of a press to obtain the contour shown in FIG. 9(c)(D), a semiconductor device is mounted on the lead frame still having the reinforcing tape attached thereon. Also, the mounted semiconductor device is encapsulated with a resin in a condition where the lead frame still has the tape. The line E11-E12 illustrates a cut portion.

The tip of the inner lead 131 of the lead frame used in the semiconductor device of this first embodiment has a cross-sectional shape as shown in FIG. 13(1)(a). The tip 131A has an etched flat surface (second surface) 131Ab which is substantially flat and therefore has a width W1 slightly greater than the width W2 of an opposite surface. The widths W1 and W2 (about 1000 μ m) are more than the width W at the central portion of the tips when viewed in the direction of the inner lead thickness. Thus, the tip of the inner lead has a cross-sectional shape having opposite wide surfaces. To this end, although either of the opposite surfaces of the tip 131A can be easily electrically connected to a semiconductor device (not shown) by a wire 120A or 120B, this embodiment illustrates the use of the etched flat surface for wire-bonding as shown in FIG. 13(D)(a). In FIG. 13, a reference numeral

131Ab depicts an etched flat surface, 131Aa a surface of a
lead frame blank, and 121A and 121B, respectively, a plated
portion. In the case of FIG. 13(D)(a), there has
particularly excellent in wire-bonding property, because
5 the etched flat surface does not have roughness. FIG.
13(A) shows that the tip 1331B of the inner lead of the
lead frame fabricated according to the process illustrated
in FIG. 14 is wire-bonded to a semiconductor device. In
this case, however, both the opposite surfaces of the tip
10 1331B of the inner lead are flat, but have a width smaller
than that in a direction of the inner lead thickness. In
addition to this, as both the opposite surfaces of the tip
1331B is formed of surfaces of the lead frame blank, these
surfaces have an inferior wire-bonding property as compared
15 to that of the etched flat surface of this first
embodiment. FIG. 13(=) shows that the inner lead tip
1331C or 1331D, obtained by thinning in its thickness by a
means of a press (coining) and then by etching, is wire-
bonded to a semiconductor device (not shown). In this
20 case, however, a pressed surface of the inner lead tip is
not flat as shown FIG. 13(=). Thus, the wire-bonding on
either of the opposite surfaces as shown in FIG. 13(=)(a)
or FIG. 13(=)(b) often results in an insufficient wire-
bonding stability and a problematic quality. The drawing
25 reference numeral 1331Ab represents a coining surface.

A modified example of the resin-encapsulated semiconductor device in accordance with the first embodiment of the present invention will be described hereinafter. FIGs. 3(a) through 3(e) are cross-sectional views of the modified example of the resin-encapsulated semiconductor device in accordance with the first embodiment of the present invention. The semiconductor device of the modified example as shown in FIG. 3(a), is different from that of the first embodiment in that a position of the die pad 135 is changed, that is, the die pad 135 is exposed to the outside. By the fact that the die pad 135 is exposed to the outside, the heat dissipation property is improved as compared to the first embodiment. Also, in the semiconductor device of the modified example as shown in FIG. 3(b), because the die pad 135 is exposed to the outside, the heat dissipation property is improved as compared to the first embodiment. Unlike the first embodiment or the modified example as shown in FIG. 3(a), in the present modified example as shown in FIG. 3(b), because a direction of the semiconductor device 110 is changed, the first surfaces of the lead frame are established as the wire bonding surfaces. The modified examples as shown in FIGs. 3(c), 3(d) and 3(e), illustrate semiconductor devices which are obtained by modifying the semiconductor devices of the first embodiment, the modified

example as shown in FIG. 3(a) and the modified example as shown in FIG. 3(b), wherein the semi-spherical solders are not used, and instead, the top surfaces of the terminal columns are directly used as the terminal portions, whereby an entire manufacturing procedure can be simplified.

Next, a resin-encapsulated semiconductor device in accordance with a second embodiment of the present invention will be described. FIG. 4(a) is a cross-sectional view of the resin-encapsulated semiconductor device in accordance with the second embodiment of the present invention, FIG. 4(b) is a cross-sectional view illustrating inner leads, taken along the line A3-A4 of FIG. 4(a), and FIG. 4(c) is a cross-sectional view illustrating a terminal column, taken along the line B3-B4 of FIG. 4(a). Because an outer appearance of the semiconductor device of the second embodiment is substantially the same as that of the first embodiment, it is not illustrated in the drawings. In FIG. 3, the drawing reference numeral 200 represents a semiconductor device, 210 a semiconductor chip, 211 electrodes (pads), 220 wires, 230 a lead frame, 231 inner leads, 231Ab a second surface, 231Ac a third surface, 231Ad a fourth surface, 233 terminal columns, 233A terminal portions, 233B side surfaces, 233S top surfaces, 240 a resin encapsulate, and 270 a reinforcing fastener tape. In the semiconductor device of

this second embodiment, the lead frame 230 does not have a die pad, the semiconductor chip 210 is fastened to the inner leads 231 by the reinforcing fastener tape 270, and the semiconductor chip 210 is electrically connected at its electrodes (pads) 211 to the second surfaces 231Ab of the inner leads 231 by wires 220. Also, in the case of this second embodiment, similarly to the first embodiment, the electrical connection between the resin-encapsulated semiconductor device 200 of this embodiment and an external circuit is achieved by mounting the resin-encapsulated semiconductor device 200 via the terminal portions 233A each being made of a semi-spherical solder, on a printed circuit substrate, with the terminal portions 233A located on the top surfaces 233S of the terminal columns 233, respectively.

In addition, the semiconductor device of this second embodiment does not have a die pad as shown in FIGs. 10(a) and 10(b). The manufacturing method of the semiconductor device of this embodiment using the lead frame 230A which is shaped by the etching process is substantially the same as that of the first embodiment except that, while in the case of the first embodiment, the wire bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip is fastened to the inner leads, in the case of the second embodiment, the wire

bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip 211 is fastened together with the inner leads 231 by the reinforcing fastener tape 270. Also, the cutting process for the unnecessary portions and the terminal portion forming process after resin encapsulating process are implemented in the same way as the first embodiment. The lead frame 230 as shown in FIG. 10(a) is obtained in the same manner by which the lead frame 130A as shown in FIG. 9(a) is obtained. In other words, by cutting the resultant structure obtained after etching the structure as shown in FIG. 10(c)(1), the contour as shown in FIG. 10(a) is obtained. At this time, the conventional reinforcing fastener tape 260 (the polyimide tape) as shown in FIG. 10(c)(2), which performs a reinforcing function is used.

FIG. 5(a) through 5(c) are cross-sectional views illustrating modified examples of the semiconductor device of the second embodiment. The semiconductor device as shown in FIG. 5(a) is different from the semiconductor device of the second embodiment, in that the surface of the semiconductor chip thereof which has the electrodes is directed downward. The modified examples as shown in FIGs. 5(b) and 5(c), illustrate semiconductor devices which are obtained by modifying the semiconductor devices of the second embodiment and the modified example as shown in FIG.

5(a), wherein the semi-spherical solders are not used, and instead, the top surfaces of the terminal columns are directly used as the terminal portions. In these examples, because a protective frame is not used and the side surfaces 333B of the terminal columns 333 are exposed to the outside, a checking operation by a test, etc. can be easily performed.

Hereinafter, a resin-encapsulated semiconductor device in accordance with a third embodiment of the present invention will be described. FIG. 6(a) is a cross-sectional view of the resin-encapsulated semiconductor device of the third embodiment, FIG. 6(b) is a cross-sectional view illustrating inner leads, taken along the line A5-A6 of FIG. 6(a), and FIG. 6(c) is a cross-sectional view illustrating a terminal column, taken along the line B5-B6 of FIG. 6(b). Because an outer appearance of the semiconductor device of the this third embodiment is substantially the same as that of the first embodiment, it is not illustrated in the drawings. In FIG. 6, the drawing reference numeral 300 represents a semiconductor device, 310 a semiconductor chip, 312 bumps, 330 a lead frame, 331 inner leads, 331Aa a first surface, 331Ab a second surface, 331Ac a third surface, 331Ad a fourth surface, 333 terminal columns, 333A terminal portions, 333B side surfaces, 333S top surfaces, 340 a resin encapsulate, and 350 a

reinforcing fastener tape. In the semiconductor device of this third embodiment, the semiconductor chip 310 is fastened to the second surfaces 331Ab of the inner leads 331 by the bumps 311 thereby to be electrically connected to the second surfaces 331Ab. The lead frame 330 has a contour as shown in FIGs. 10(a) and 10(b), which is formed by the etching process of FIG. 11. As shown in FIG. 13(1)(b), both widths W1A and W2A (about 100 μ m) at top and bottom ends of the inner leads 331 are larger than a width WA at a center portion in a thickness-wise direction. Due to the fact that the second surfaces 331Ab of the inner leads 331 is depressed toward the inside of the inner leads and the first surfaces 331Aa are flat, a desired fineness can be obtained. Also, when the second surfaces 331Ab of the inner leads 331 are electrically connected to the semiconductor chip via bumps, easy connection can be accomplished as shown in FIG. 13(2)(b). Further, in the case of this third embodiment, as in the case of the first and second embodiments, the electrical connection between the resin-encapsulated semiconductor device 300 of this embodiment and an external circuit is achieved by mounting the resin-encapsulated semiconductor device 300 via the terminal portions 333A each being made of a semi-spherical solder, on a printed circuit substrate, with the terminal portions 333A located on the top surfaces of the terminal

columns 333, respectively.

In addition, unlike the semiconductor device of the first embodiment, the semiconductor device of this third embodiment uses a lead frame which is shaped by the etching process as shown in FIG. 12. However, the manufacturing method of the semiconductor device of this embodiment is substantially the same as that of the first embodiment except that, while in the case of the first embodiment, the wire bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip is fastened to the inner leads, in the case of this third embodiment, the wire bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip 310 is fastened to the inner leads 331 via the bumps. Also, the cutting process for the unnecessary portions and the terminal portion forming process after resin encapsulating process are implemented in the same way as the first embodiment.

FIG. 6(d) is a cross-sectional view illustrating a modified example of the semiconductor device in accordance with the third embodiment of the present invention. In the modified example of the semiconductor device as shown in FIG. 6(d), the terminal portions each comprising the semi-spherical solder are not provided, and the top surfaces of the terminal columns are directly used as the terminal

portions. Because the protective frame is not used and the side surfaces 333B of the terminal columns 333 are exposed to the outside, a checking operation by a test, etc. can be easily performed.

5 Hereinafter, a resin-encapsulated semiconductor device in accordance with a fourth embodiment of the present invention will be described. FIG. 7(a) is a cross-sectional view of the resin-encapsulated semiconductor device of the fourth embodiment, FIG. 7(b) is a cross-sectional view illustrating inner leads, taken along the line A7-A8 of FIG. 7(a), and FIG. 7(c) is a cross-sectional view illustrating a terminal column, taken along the line 10 B7-B8 of FIG. 7(b). Because an outer appearance of the semiconductor device of the this fourth embodiment is substantially the same as that of the first embodiment, it is not illustrated in the drawings. In FIG. 7, the drawing 15 reference numeral 400 represents a semiconductor device, 410 a semiconductor chip, 411 pads, 430 a lead frame, 431 inner leads, 431Aa a first surface, 431Ab a second surface, 431Ac a third surface, 431Ad a fourth surface, 433 terminal columns, 433A terminal portions, 433B side surfaces, 433S top surfaces, 440 a resin encapsulate, and 470 insulating adhesive. In the semiconductor device of this fourth 20 embodiment, one surface of the semiconductor chip 410 on which the pads 411 are disposed is fastened to the second 25

surfaces 431Ab of the inner leads 431 by the insul-
adhesive 470, and the pads 411 and the first surfaces
of the inner leads 431 are electrically connected with
other by wires 420. The semiconductor device of
5 fourth embodiment uses the same lead frame which is use
the third embodiment, which has the contour as shown
FIG. 10(a) and 10(b). Also, in the case of this fourth
embodiment, as in the case of the first and second
embodiments, the electrical connection between the res-
10 encapsulated semiconductor device 400 of this embodiment
and an external circuit is achieved by mounting the res-
encapsulated semiconductor device 400 via the terminal
portions 433A each being made of a semi-spherical solder
on a printed circuit substrate, with the terminal portion
15 433A located on the top surfaces of the terminal columns
433, respectively.

FIG. 7(d) is a cross-sectional view illustrating
modified example of the semiconductor device in accordance
with the fourth embodiment of the present invention. In
20 the modified example of the semiconductor device as shown
in FIG. 7(d), the terminal portions each comprising the
semi-spherical solder are not provided, and the top
surfaces of the terminal columns are directly used as the
terminal portions. Because the protective frame is not
25 used and the side surfaces 433B of the terminal columns 433

are exposed to the outside, a checking operation by a test, etc. can be easily performed.

(EFFECTS OF THE INVENTION)

5 The present invention provides a resin-encapsulated semiconductor device employing the above-mentioned lead frame, which is capable of meeting a demand for the increased terminal number. Furthermore, the resin-encapsulated semiconductor device in accordance with this
10 invention does not require a process of cutting or bending the dam bars as in the case of using a lead frame having outer leads as shown in FIG. 13(b). As a result of this, the resin-encapsulated semiconductor device does not have a problem in that the outer leads are bent, or a problem
15 associated with coplanarity. In addition to these advantages, the resin-encapsulated semiconductor device has a shortened interconnection length as compared to the QTP or the BGA, whereby the semiconductor device can be reduced in a parasitic capacity, and shortened in a transfer delay
20 time.

591343 v1

591343 v1

(11) 47 = 822 = 4

(1) 公明 案 (1997) : A : C =

此所表示は

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【実施例 1】

2 段ニッチング加工によりインターリードの厚さがリードフレーム素材の厚さより厚肉に形成されたリードフレームを用いた半導体装置であつて、前記リードフレームは、リードフレーム素材より厚肉のインターリードと、該インターリードに一体的に連結したリードフレーム素材と同じ厚さの外側面壁とを形成するための厚さの端子柱とを有し、且つ、端子柱はインターリードの外側面においてインターリードに対して厚み方向に直立して設けられており、端子柱の先端部は半導体からなる端子部を露け、端子部を防止層層壁から露出させて、端子柱の外側面の側面を防止層層壁から露出させており、インターリードは、断面形状が長方形で第 1 面、第 2 面、第 3 面、第 4 面の 4 面を有しており、かつ第 1 面はリードフレーム素材と同じ厚さの他の部分の一方の面と同一平面上にあって第 2 面に向を合っており、第 3 面、第 4 面はインターリードの内側に向かつて凹んだ形状に形成されていることを特徴とする層状封止型半導体装置。

【実施例 2】 2 段ニッチング加工によりインターリードの厚さがリードフレーム素材の厚さより厚肉に形成されたリードフレームを用いた半導体装置であつて、前記リードフレームは、リードフレーム素材より厚肉のインターリードと、該インターリードに一体的に連結したリードフレーム素材と同じ厚さの外側面壁とを形成するための厚さの端子柱とを有し、且つ、端子柱はインターリードの外側面においてインターリードに対して厚み方向に直立して設けられており、端子柱の先端の一部を防止層層壁から露出させて端子部とし、端子柱の外側面の側面を防止層層壁から露出させており、インターリードは、断面形状が長方形で第 1 面、第 2 面、第 3 面、第 4 面の 4 面を有しており、かつ第 1 面はリードフレーム素材と同じ厚さの他の部分の一方の面と同一平面上にあって第 2 面に向を合っており、第 3 面、第 4 面はインターリードの内側に向かつて凹んだ形状に形成されていることを特徴とする層状封止型半導体装置。

【実施例 3】 図 1 ないし 2 において、半導体素子はインターリード間に設けられ、該半導体素子の電極部はワイヤにてインターリードと電気的に接続されていることを特徴とする層状封止型半導体装置。

【実施例 4】 図 3 において、リードフレームはダイパッドを有しており、半導体素子はダイパッド上に搭載され、固定されていることを特徴とする層状封止型半導体装置。

【実施例 5】 図 4 において、リードフレームはダイパッドを有しないので、半導体素子はインターリードとともに直接固定用テープにより固定されていることを特徴とする層状封止型半導体装置。

【実施例 6】 図 1 ないし 2 において、半導体素子は半導体素子の電極部側の面をインターリードの第 2 面

に施した層状構造により固定されており、該半導体素子の電極部はワイヤにてインターリードの第 1 面と電気的に接続されていることを特徴とする層状封止型半導体装置。

【実施例 7】 図 1 ないし 2 において、半導体素子はバンプによりインターリードの第 2 面に固定されて電気的にインターリードと接続していることを特徴とする層状封止型半導体装置。

【発明の効果】

(0001)

【従来の技術】 本発明は、半導体素子の多量化に対応して、且つ、アフターリードの低コスト化（ミニチュア）やアフターリードの半導体（コプラチニウム）の低コスト化による、リードフレームを用いた層状封止型半導体装置に関する。

(0002)

【従来の技術】 従来の層状封止型半導体装置（プラスチックリードフレームパッケージ）は、一面に図 1 (a) に示されるような構造であり、

半導体素子 1510 を搭載するダイパッド部 1511 の両側の面壁と電気的に接続を行うためのアフターリード部 1513、アフターリード部 1513 に一体となったインターリード部 1512、該インターリード部 1512 の先端部と半導体素子 1520 の電極パッド 1521 とを電気的に接続するためのワイヤ 1530、半導体素子 1520 を封止して外部からの応力、腐食から守る層 1540 からなっており、半導体素子 1520 をリードフレームのダイパッド 1511 上に搭載した場合には、層 1540 により封止してパッケージとしたもので、半導体素子 1520 の電極パッド 1521 に対応する数のインターリード部 1512 を必要とするものである。そして、このような層状封止型の半導体装置の製造工程として用いられる（本発明）リードフレームは、一面

には図 1 (b) に示すような構造のもので、半導体素子を搭載するためのダイパッド 1511 と、ダイパッド 1511 の両面に設けられた半導体素子とを接続するためのインターリード部 1512、該インターリード部 1512 に連続して外側面壁との電極を行うためのアフターリード部 1513、層状封止する際のダムとなるダム部 1514、リードフレーム 1510 全体を支持するフレーム（本）部 1515 を備えており、図 1 (b) の 4 2 番金（42 ミニマル・金）は、図 1 (b) のような構造に備えられた金を用い、プレス加工してエッチング法により形成されていた。図 1 (b) (c) は、図 1 (b) (イ) に示すリードフレームを第 1 図の F1-F2 における断面図である。

(0003) このようなリードフレームを用いた層状封止型の半導体装置（プラスチックリードフレームパッケージ）において、半導体素子の電極部側の面壁と半導体素子の電極部との間に、小間隔化かつ電極部との

増大が望んで、その結果、能率向上が図られた。次に QFP (Quad Flat Package) 及び TQFP (Thin Quad Flat Package) 等では、リードの多ピン化が著しくなってきた。上記の半導体装置に用いられるリードフレームは、従来ものはフォトリソグラフィ工程を用いたエッチング加工方法により作製され、従来でないものはプレスによる加工方法により作製されるのが一般的であったが、このような半導体装置の多ピン化に伴い、リードフレームにおいても、インナーリード部実装の複雑化が進み、従来は、従来ものに対しては、プレスによる加工方法加工により、リードフレーム部材の厚さが 0.25 mm 程度のものを用い、エッチング加工で対応してきた。このエッチング加工工程の工程について以下、図 14 に基づいて簡単に述べておく。先ず、図 14 (a) には 42% ニッケル-鉄合金からなる厚さ 0.25 mm 程度の厚板 (リードフレーム部材 1410) を示す (図 14 (a))。したは、厚さ 0.25 mm の厚板を感光剤として感光剤でインレジスト層のフォトリソグラフィ工程の製造工程に併せて塗布する。(図 14 (b))。次に、所定のパターンが形成されたマスクを介して感光剤層でレジスト層を露光した。所定の露光量で感光剤層レジストを露光して (図 14 (c))、レジストパターン 1430 を形成した。露光工程は露光装置を必要に応じて行い、感光剤層の厚さを 3 層とする。エッチング工程にて、スプレーにて感光剤 (リードフレーム部材 1410) に所定の寸法精度にエッチングし、所定させる。(図 14 (d))。次に、レジスト層を剥離処理 (図 14 (e))。剥離後、所定のリードフレームを得て、エッチング加工工程を終了する。このように、エッチング加工工程により作製されたリードフレームは、更に、所定のエリアに感光剤層が形成される。よって、感光剤層の形成を終了して、インナーリード部実装用の露光工程をシリミドテープにてテーピング処理したり、必要に応じて所定のスタブワイヤーを曲げ加工し、ダイパッド部をダウンセットする処理を行う。しかし、エッチング加工工程においては、エッチング液による腐食は加工工程の進行に伴って腐蝕 (腐) 方向にも進むため、その腐蝕加工にも腐蝕があるのが一般的で、図 14 に示すように、リードフレーム部材の両面からエッチングするため、ラインエッチングによる腐蝕が、ライン間隔が加工精度に、厚さの 50~100% 程度と示されている。又、リードフレームの加工工程のアフターリードの位置を考えた場合、一般的には、その厚さは約 0.125 mm 以上必要とされている。このため、図 14 に示すようなエッチング加工工程の場合、リードフレームの厚さを 0.15 mm~0.125 mm 程度まで減らすことにより、ワイヤボンディングのための必要な厚さを 70~80 μm を確保し、0.165 mm ピッチ程度の通常のインナー

リード部実装のエッチングによる加工を達成してきたが、これが限度とされていた。
(0004) しかしながら、近年、厚さ 0.1 mm 程度の薄板は、小パッケージでは、半導体であるインナーリードのピッチが 0.165 mm ピッチを見て、既に 0.15~0.13 mm ピッチまでのピッチ化が要求されてきた。エッチング加工において、リード部材の厚さを減らした場合には、アフターリード部実装工程において加工工程におけるアフターリードの位置精度が著しく低下するから、更にリード部材の厚さを減らしてエッチング加工を行う方法にも限界が出てきた。
(0005) これに対応する方法として、アフターリードの位置を調整したまま腐蝕を行う方法で、インナーリード部実装をハーフエッチングもしくはプレスにより減らしてエッチング加工を行う方法が提案されている。しかし、プレスにより減らしてエッチング加工をやる場合場合には、加工工程においての厚さが不足する (例えば、ワイヤボンディングのクランプに必要なインナーリードの厚さ、厚さの厚さが確保されない、腐蝕を 2 度行なわなければならない腐蝕工程が複雑になる、腐蝕量が多くなる、そして、インナーリード部実装をハーフエッチングにより減らしてエッチング加工を行う方法の場合にも、腐蝕を 2 度行なわなければならない腐蝕工程が複雑になるといふ問題があり、いずれも実用化には、まだ至っていないのが現状である。
(0006)
(見解が及ぶようとする場合は「半導体装置の多ピン化に伴いインナーリードピッチが低くなり、半導体装置を実装する際に、アフターリードの位置ズレ (スキュー) や腐蝕 (コブラリティー) の発生が顕著となる」として、本見解は、このような状況のもと、多ピン化に対応して、又、アフターリードの位置ズレ (スキュー) や腐蝕 (コブラリティー) の発生にも対応できる半導体装置の製造をしようとするものである。
(0007)
(問題を解決するための手段) 本見解の腐蝕防止型半導体装置は、エッチング加工によりインナーリードの厚さがリードフレーム部材の厚さよりも厚く加工されたリードフレームを用いた半導体装置であって、前記リードフレーム部材のインナーリード部は、インナーリードと、インナーリードに一体的に形成したリードフレーム部材と同じ厚さの厚さ部材とを有する。また、前記厚さ部材はインナーリードの厚さ部材においてインナーリードに対して厚さ方向に延びて形成されており、厚さ部の先端部に半導体からなる端子部を設け、端子部を半導体装置から露出させ、厚さ部の厚さ部材の厚さを半導体装置から露出させており、インナーリードは、断面形状が矩形で、

(4)

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て、テーピングの工程や、リードフレームを固定するウラン工程で、ベタはに腐蝕され部分的に腐くなった部分との段差が原因になる場合があるので、エッチングを行うエリアはインナーリード先の追加加工部分だけにせず大めにとる必要がある。従って、温度 57°C 、比重 4.8 のホウ酸化第二硫酸溶液を用いて、スプレー $2.5\text{kg}/\text{cm}^2$ にて、レジストパターンが形成されたリードフレーム 1110 の両面にエッチングし、ベタは (平塩化) に腐蝕された第一の凹部 1150 の底面がリードフレーム部の約 $2/3$ 程度に達した時点でエッチングを止めた。(図 11 (b))

上記第 1 回目のエッチングにおいては、リードフレーム部 1110 の両面から同時にエッチングを行ったが、必ずしも両面から同時にエッチングする必要はない。本実験例のように、第 1 回目のエッチングにおいてリードフレーム部 1110 の両面から同時にエッチングする理由は、両面からエッチングすることにより、段差を第 2 回目のエッチング時間を短縮するため、レジストパターン 9208 部からのみの片面エッチングの場合と比べ、第 1 回目エッチングと第 2 回目エッチングのトータル時間が短縮される。従って、第一の凹部 1130 部の両面に腐蝕された第一の凹部 1150 部にエッチング液 1180 としての銅エッチング液のあるホットメルト型ワックス (ブレイクテック社製のワックス、型番 MR-W86) を、ダイコータを用いて、塗布し、ベタは (平塩化) に腐蝕された第一の凹部 1150 部に埋め込んだ。レジストパターン 1120A 上もエッチング液 1180 に腐蝕された状態とした。(図 11 (c))

エッチング液 1180 を、レジストパターン 1120A と完全に塗布する必要はないが、第一の凹部 1150 を含む一面にのみ塗布することにした。図 11 (c) に示すように、第一の凹部 1150 とともに、第一の凹部 1130 部全面にエッチング液 1180 を塗布した。本実験例で使用するエッチング液 1180 は、アルカリ性銅製のワックスであるが、基本的にエッチング液に銅板があり、エッチング時にある程度の腐蝕作用のあるものが好ましく、特に、上記ワックスに腐蝕されて U.V. 硬化型のものではない。このようにエッチング液 1180 をインナーリード先の両面を腐蝕するためのパターンが形成された底面の両面に第一の凹部 1150 部を塗布することにより、第二回目のエッチング時に第一の凹部 1150 が腐蝕されて大々くならないようにしていることと、両面からエッチング加工に対しての腐蝕的な効果を得ており、スプレーを $2.5\text{kg}/\text{cm}^2$ (以上) とすることができ、これによりエッチングが底面に達しやすくなる。この後、第 2 回目のエッチングを行う「ベタは (平塩化) に腐蝕された第二の凹部 1160 部両面からリードフレーム部 1110 をエッチングし、再度で、

インナーリード先部 131A を形成した。(図 11 (c))

第 1 回目のエッチング加工にて作成された、リードフレーム面に平面的なエッチング液底面に平面的であるが、この底面を 2 面はインナーリード側にへこんだ凹部である。従って、通常、エッチング液 9208 の第 3 レジスト部 (レジストパターン 1120A 、 1120B) の両面を所い、インナーリード先部 131A が形成された図 9 (a) に示すリードフレーム 130A を用いた、エッチング液 1180 とレジスト部 (レジストパターン 1120A 、 1120B) の第 3 面に平面的なリードフレーム部により腐蝕された。

(0014) 上記、図 11 に示すリードフレームの腐蝕状態は、本実験例に用いられる、インナーリード先部を両面から腐蝕したリードフレームをエッチング加工により腐蝕する状態で、特に、図 11 に示す、インナーリード先の第一凹部 131A を両面から腐蝕した状態の第一凹部 131A と 131A と対向させて腐蝕し、且つ、第 3 面 131A と、第 4 面 131A をインナーリードの内側に向かって凹んだ状態にするエッチング加工方法である。従って本実験例の腐蝕状態のようにパンプを用いて本実験例をインナーリードの第 2 面 131A 部に腐蝕し、インナーリードと電気的に接続する場合に

に、第 2 面 131A をインナーリード側に凹んだ状態に腐蝕した方がパンプ腐蝕の部の腐蝕度が大々くとなる。図 12 に示すエッチング加工方法が図 12、図 12 に示すエッチング加工方法は、第 1 回目のエッチング工程までは、図 11 に示す方法と同じであるが、エッチング液 1180 を第二の凹部 1160 部に埋め込んだ後、第一の凹部 1150 部から第 2 回目のエッチングを行い、腐蝕をより進めようとしている。第 1 回目のエッチングにて、第二凹部 1160 からのエッチングを充分に行うべく、図 12 に示すエッチング加工方法によって得られたリードフレームのインナーリード先の腐蝕状態は、図 6 (b) に示すように、第 2 面 131A がインナーリード側にへこんだ凹部になる。

(0015) 以上、上記第 11、図 12 に示すエッチング加工方法のように、エッチングを 2 段階にわたって行うエッチング加工方法を、一般には 2 段階エッチング加工方法という。本加工工程に有利な加工方法である。本実験例に用いた図 9 (b) に示す、リードフレーム 130A の両面においては、2 段階エッチング加工方法、パターン形成を加工することにより部分的にリードフレーム部を腐蝕しながら本加工をする方法とが採用されている。リードフレーム部を腐蝕した部分においては、特に、腐蝕加工がどうようにしている。図 11、図 12 に示す、上記の方法においては、インナーリード先部 131A の腐蝕加工は、第二の凹部 1160 の両面と、腐蝕的に腐蝕されるインナーリード先部の両面に腐蝕されるので、例えば、腐蝕 150um

〔0019〕、次いで、実施例2の本発明の型番を決定
する。図4(a)に実施例2の型番決定型番決定
表の新図面であり、図4(b)に図4(a)のA3-A-
4におけるインターリード部の新図面、図4(c)は
図4(a)のB3-B4における端子配列の新図面であ
る。尚、実施例2の型番決定表の列は、実施例1と同一
の値となる。図には省略した、210に型番
決定、210は型番決定、211は型番(パッ
ド)、220はワイヤ、230はリードフレーム、23
1はヤンナーリード、231Aは第1面、231A5-
は第2面、231A6は第3面、231A7は第4面、
233は端子配列、233Aは端子部、233Bは第
1面、233Cは第2面、240は禁止用符号、270は
型番決定型番決定表、実施例2の型番決定表におい
 ては、リードフレーム230はダイパッドを付さない
で、型番決定210はヤンナーリードであり、これに
 型番決定型番決定表270により決定されてあり、型
番決定210は、型番決定の型番(パッド)211

10025) において、実施例4の第11止型ニズエズ
をける。図7(a)は実施例4の第11止型ニズエズ
の断面図であり、図7(b)は図7(a)のA7-A
8におけるインターリード部の断面図で、図6(c)に
図6(a)の87-98における底面E部の断面図であ
る。図7(c)は実施例4の第11止型ニズエズの
断面図である。図7(d)は、図7(c)に示す部
位、410に示す部にて、411にパッド、430に

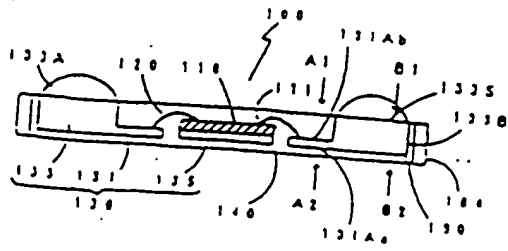
190	ードフレイムニ面	
260	1331A6	
270	イニング面	
270	1410	
270	ードフレイムニ面	
270	1420	
270	オートレジスト	
270	1430	
270	ジストパターン	
270	1440	
270	ンナーリード	
270	1510	
270	ードフレイム	
270	1511	
270	イパッド	
270	1512	
270	ンナーリード	
270	1512A	
270	ンナーリード先頭部	
270	1513	
270	ワターリード	
270	1514	
270	ムパー	
270	1515	
270	レーン部 (パッド)	
270	1520	
270	ニ面部	
270	1521	
270	ニ面部 (パッド)	
270	1530	
270	1540	
270	止用面	

(11)

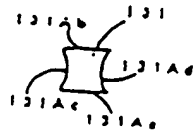
425-0000

(21)

(a)



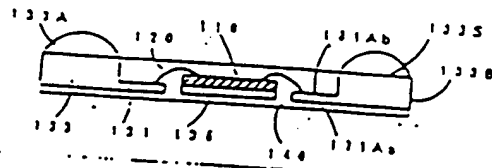
(b)



(c)

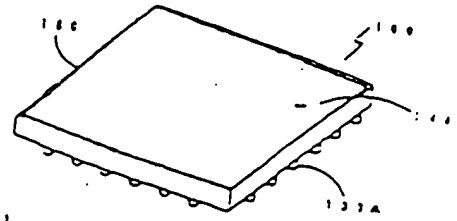


(d)

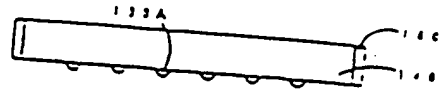


(22)

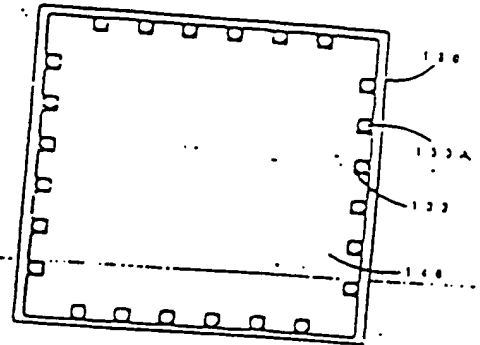
(a)



(b)

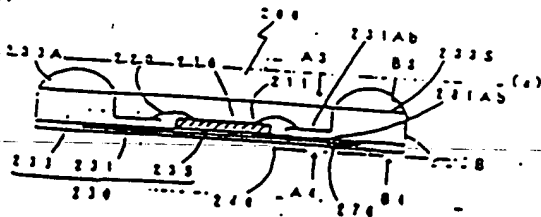


(c)

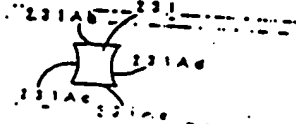


(24)

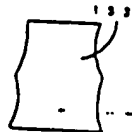
(a)



(b)

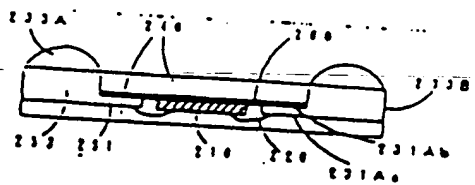


(c)

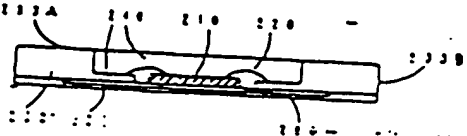


(25)

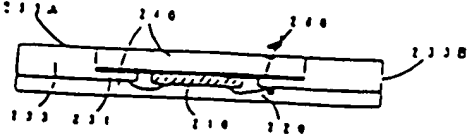
(a)



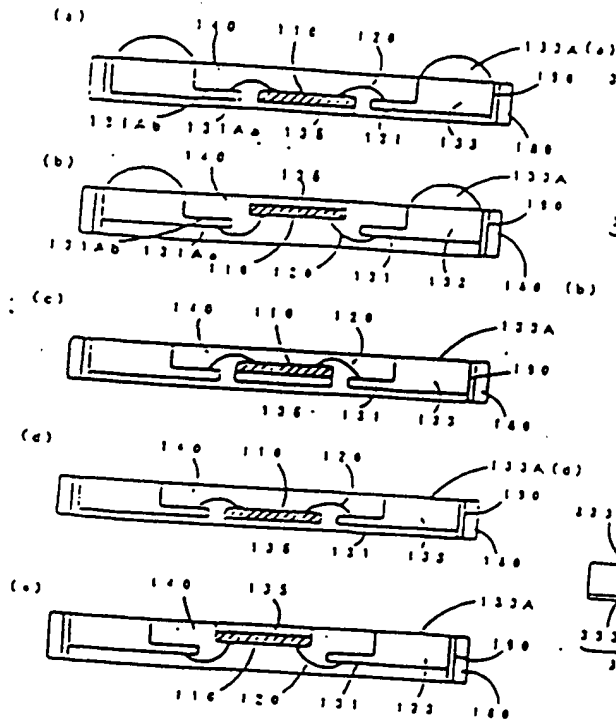
(b)



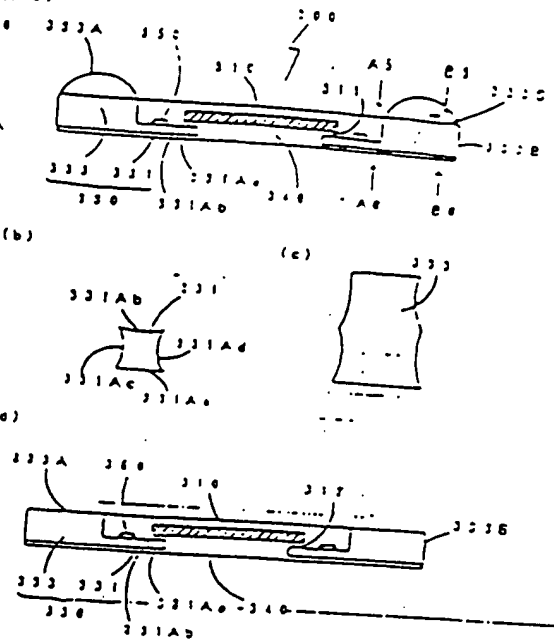
(c)



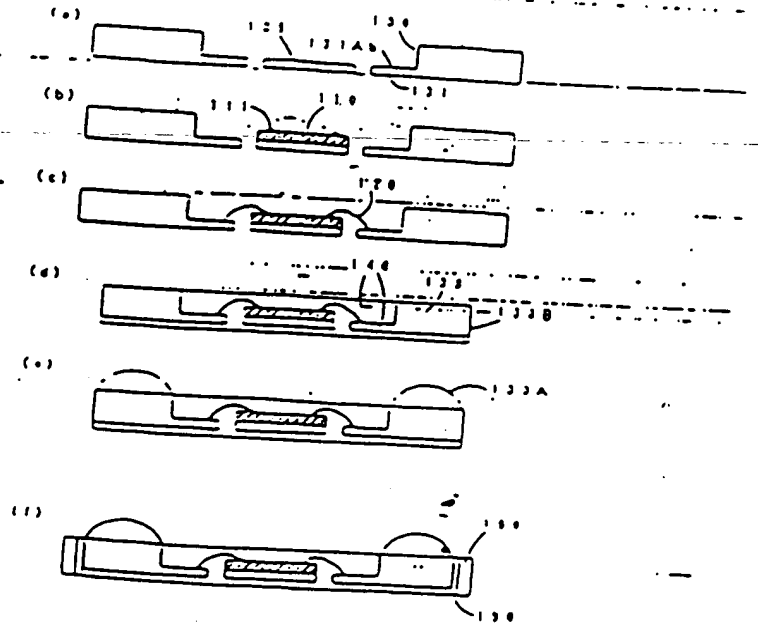
(22)



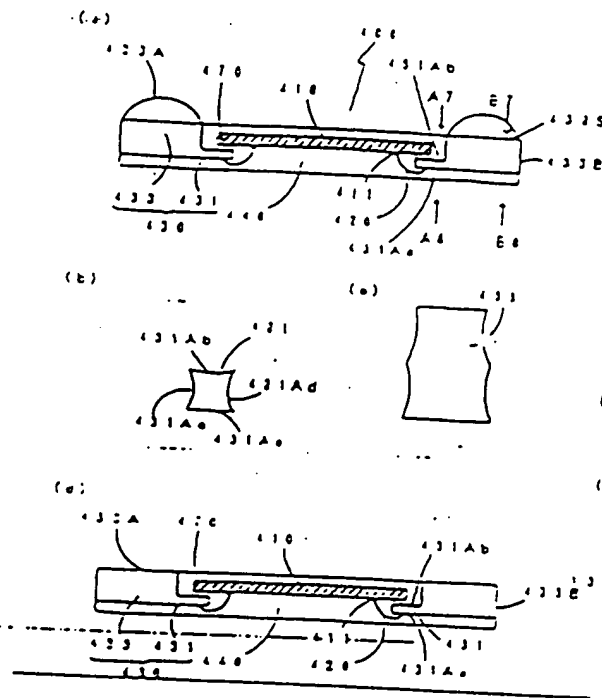
(26)



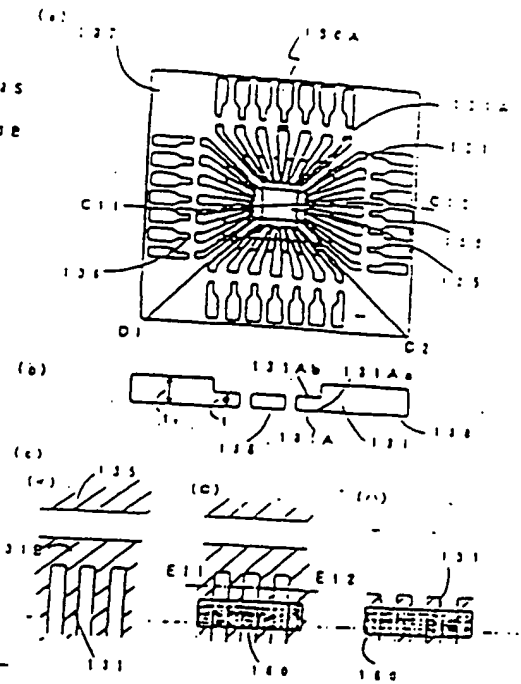
(23)



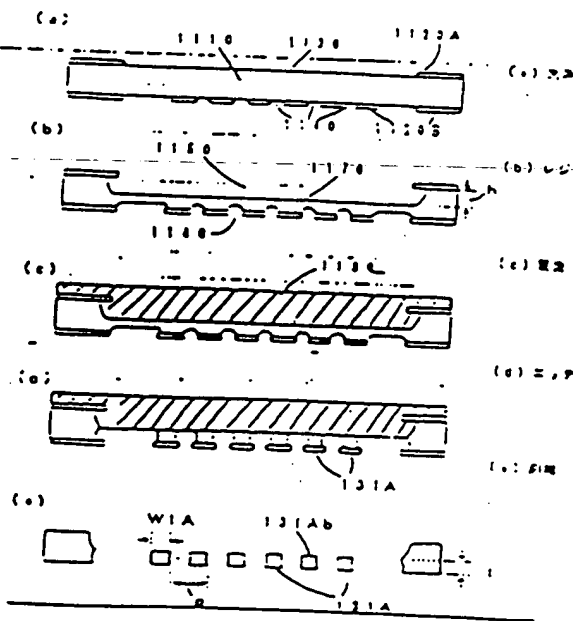
(27)



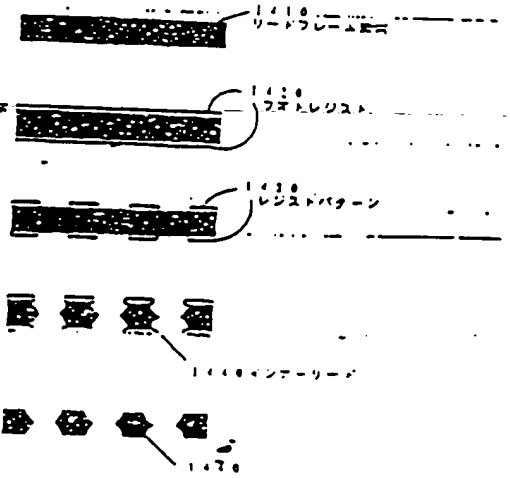
(28)



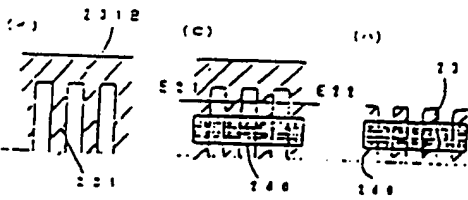
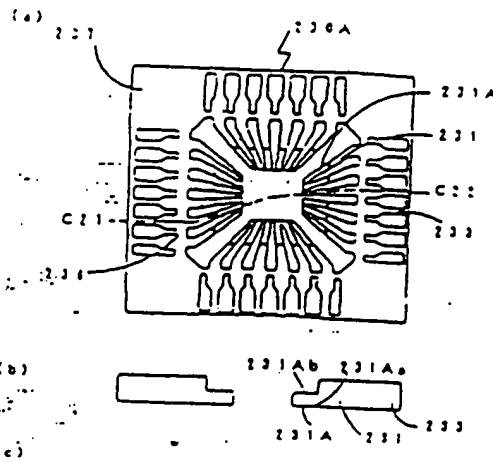
(29)



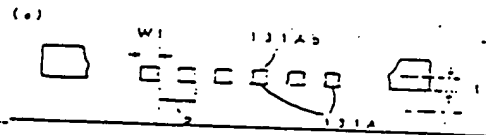
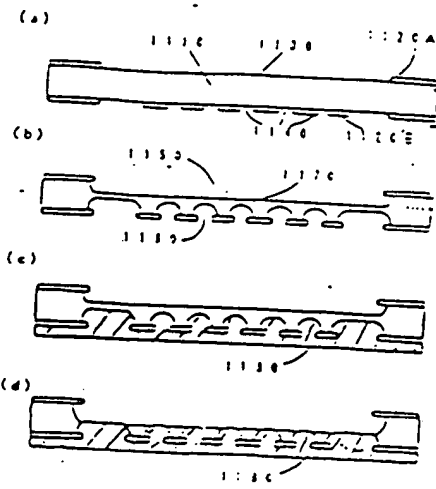
(30)



(210)



(212)



(215)

